

U.S. Department of Commerce, Patent and Trademark				Atty. Docket No.		Application No.		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				BTAT.002US1		09/832,933		
				Applicant(s)		Conf. No.		
(Use several sheets if necessary)				Wu et al.		5253		
(Form PTO-1449)				Filing Date		Art Group		
				April 11, 2001		2123		
U.S. Patent Documents								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
TS	1	7,003,755	2/2006	Pang et al.				
TS	2	6,209,122	03/2001	Jyu et al.				
TS	3	6,058,496	05/2000	Gillis et al.				
TS	4	6,524,872	02/2003	Cheung				
TS	5	5,600,844	02/1997	Shaw et al.				
U.S. Published Patent Application Documents								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
Foreign Patent Documents								
							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)								
TS	6	Kuo, et al., "Simulation of MOSFET Lifetime under AC Hot-Electron Stress," <i>IEEE Transactions on Electron Devices</i> , Vol. 35, No. 7, July, 1988, pp. 1004-1011.						
TS	7	Chen, "A Unified Compact Scalable Id Model for Hote Carrier Reliability Simulation," <i>IEEE</i> , March 1999, pp. 243-248.						
TS	8	Leblebici et al., "An Integrated Hot-Carrier Degradation Simulator for VLSI Reliability Analysis," <i>Proceeding ICCAD, IEEE</i> , 1990, pp. 400-403.						
TS	9	Quader et al., "Hot-Carrier-Reliability Design Rules for Translating Device Degradation to CMOS Digital Circuit Degradation," <i>IEEE Transactions on Electron Devices</i> , Vol. 41, No. 4, May 1994, pp. 681-691.						
Examiner			Date Considered /Thomas Stevens/ (12/04/2006)					
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